

TOSHIBA

2SD1222

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS) (DARLINGTON)

2SD1222

SWITCHING APPLICATIONS

HAMMER DRIVE, PULSE MOTOR DRIVE APPLICATIONS

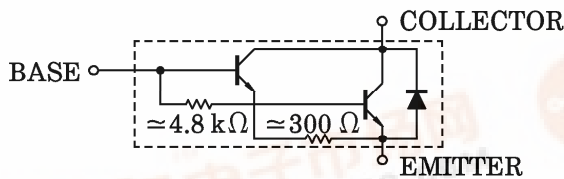
POWER AMPLIFIER APPLICATIONS

- High DC Current Gain
: $h_{FE}(1) = 2000$ (Min.)
- Low Saturation Voltage : $V_{CE(sat)} = 1.5$ V (Max.)
- Complementary to 2SB907.

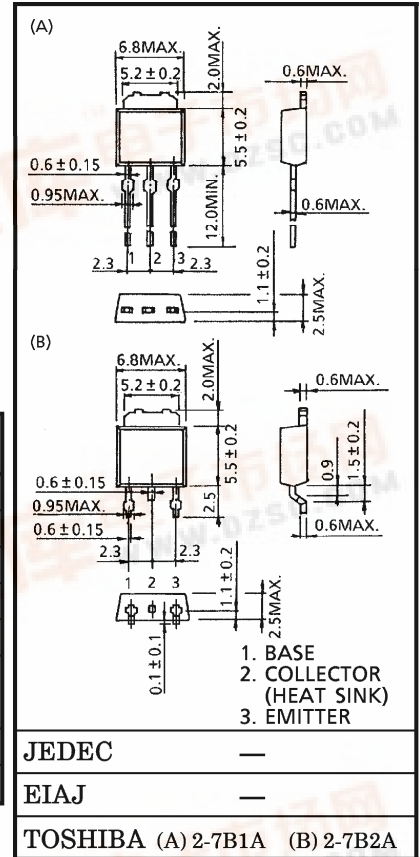
MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	3	A
Base Current	I_B	0.3	A
Collector Power Dissipation	P_C	$T_a = 25^\circ\text{C}$	1.0
		$T_c = 25^\circ\text{C}$	15
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

EQUIVALENT CIRCUIT



Unit in mm



Weight : 0.36 g (Typ.)

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 60\text{ V}, I_E = 0$	—	—	20	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	2.5	mA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C = 25\text{ mA}, I_B = 0$	40	—	—	V
DC Current Gain		$h_{FE(1)}$	$V_{CE} = 2\text{ V}, I_C = 1\text{ A}$	2000	—	—	
		$h_{FE(2)}$	$V_{CE} = 2\text{ V}, I_C = 3\text{ A}$	1000	—	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 2\text{ A}, I_B = 4\text{ mA}$	—	—	1.5	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 2\text{ A}, I_B = 4\text{ mA}$	—	—	2.0	V
Switching Time	Turn-on Time	t_{on}	<p>$I_{B1} = -I_{B2} = 6\text{ mA}$, DUTY CYCLE $\leq 1\%$</p>	—	0.1	—	μs
	Storage Time	t_{stg}		—	1.0	—	
	Fall Time	t_f		—	—	0.2	

